A N Anagnostopoulos

List of Publications by Year
in descending order

32	525	623734 14	677142 22
papers	citations	h-index	g-index

34	34	34	367
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A Digital Nonautonomous Chaotic Oscillator Suitable for Information Transmission. IEEE Transactions on Circuits and Systems II: Express Briefs, 2013, 60, 887-891.	3.0	3
2	IN-OUT INTERMITTENT LOSS OF SYNCHRONIZATION IN TWO UNIDIRECTIONALLY COUPLED NONLINEAR FOURTH-ORDER AUTONOMOUS CIRCUITS. International Journal of Bifurcation and Chaos in Applied Sciences and Engineering, 2010, 20, 3329-3339.	1.7	1
3	Digital Chaotic Synchronized Communication System. Journal of Engineering Science and Technology Review, 2009, 2, 82-86.	0.4	15
4	THE INTERMITTENCY ROUTE TO CHAOS OF AN ELECTRONIC DIGITAL OSCILLATOR. International Journal of Bifurcation and Chaos in Applied Sciences and Engineering, 2008, 18, 1561-1566.	1.7	26
5	Dielectric behavior of mixed HgBrxI2â^'x single crystals. Journal of Materials Science Letters, 2000, 19, 1019-1020.	0.5	4
6	Electrical properties of an a-Si/Si(p)/Si(n) heterojunction device. Semiconductor Science and Technology, 2000, 15, 980-984.	2.0	4
7	Current pulses and high-frequency oscillations in a-Si/Si(p)/Si(n) heterojunction device. Semiconductor Science and Technology, 1999, 14, 897-900.	2.0	4
8	DIFFUSIONAL MODEL FOR NOISY ONâ€"OFF INTERMITTENCY. International Journal of Bifurcation and Chaos in Applied Sciences and Engineering, 1999, 09, 355-359.	1.7	2
9	Single crystal growth and characterization of narrow-gap - mixed crystals. Semiconductor Science and Technology, 1998, 13, 86-92.	2.0	9
10	Optical investigation of SnS2 single crystals. Journal of Materials Science, 1996, 31, 5975-5978.	3.7	29
11	Growth and characterization of SnSe2. Journal of Materials Science, 1996, 31, 3647-3649.	3.7	19
12	Large single-crystal growth and characterization of the narrow-gap semiconductor. Semiconductor Science and Technology, 1996, 11, 1405-1410.	2.0	16
13	Analysis of microhardness data in TlxIn1â^'xSe. Journal of Materials Science, 1995, 30, 5576-5580.	3.7	10
14	Conduction anisotropy in layered semiconductors. Physical Review B, 1994, 50, 14643-14646.	3.2	17
15	Excitonic and other interband transitions inTlInS2single crystals. Physical Review B, 1994, 50, 7488-7494.	3.2	50
16	Quasiperiodic and chaotic self-excited voltage oscillations inTlInTe2. Physical Review B, 1994, 49, 16994-16998.	3.2	31
17	Negative-differential-resistance effects in theTlGaTe2ternary semiconductor. Physical Review B, 1993, 47, 4261-4267.	3.2	55
18	Nonlinear electrical conductivity ofV2O5single crystals. Physical Review B, 1992, 45, 11627-11631.	3.2	17

#	Article	IF	Citations
19	Chaotic voltage oscillations in the negative-differential-resistance region of theI-Ucurves ofV2O5crystals. Physical Review B, 1992, 46, 16144-16147.	3.2	7
20	I-Udependence of TlInX2(X=Se,Te) single crystals: The Ohmic andS-type regions. Physical Review B, 1991, 43, 4135-4140.	3.2	65
21	Temperature dependence of the energy gap and some electrical properties of Zn2In2S5(II) single crystals. Semiconductor Science and Technology, 1989, 4, 536-542.	2.0	10
22	Electronic behavior ofGa2/3PS3single crystals. Physical Review B, 1988, 37, 4026-4031.	3.2	4
23	Electrical behavior of extended twins present in layered GeSe. Journal of Applied Physics, 1986, 59, 2859-2862.	2.5	8
24	Electrical effects associated with the ordering process in CdInGaS4 crystals. II. Electron traps determined with conductivity measurements. Physica Status Solidi A, 1985, 92, 231-235.	1.7	2
25	Electrical conductivity of layered GeSe related to extended faults. Journal of Applied Physics, 1985, 58, 3917-3920.	2.5	18
26	Influence of composition faults on the AC conductivity of ZnIn2S4 (III). Physica Status Solidi A, 1983, 75, 595-599.	1.7	10
27	Comparison of the Structure and the Electric Properties of ZnIn2S4 (III)- and CdInGaS4-Layered Crystals. Physica Status Solidi A, 1983, 77, 595-601.	1.7	18
28	Voltage-Dependent Conductivity along thec-Axis of ZnIn2S4(III). Physica Status Solidi A, 1983, 79, 513-516.	1.7	5
29	Electrical effects associated with the ordering process in CdInGaS4 crystals. I. Electron microscopy and electron diffraction study. Physica Status Solidi A, 1983, 80, 503-511.	1.7	11
30	Electron trap distribution determined by means of conductivity measurements on highly anisotropic Znin2S4 crystals. Physica Status Solidi A, 1982, 71, 543-548.	1.7	9
31	Composition Faults in ZnIn2S4(III) Layered Crystals and Their Influence on the Anisotropic Conductivity of This Compound. Physica Status Solidi A, 1982, 72, 731-736.	1.7	31
32	Influence of Composition Faults on the Anisotropic Conductivity of Layered Semiconductors. Physica Status Solidi A, 1982, 73, 91-94.	1.7	10